



Thyristor Module

JMT320KT18T3

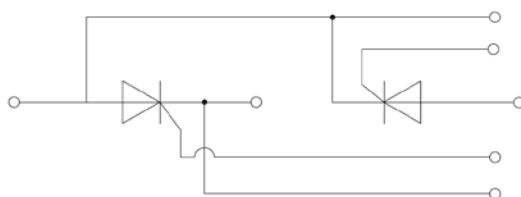
Summary

- Half-bridge SCR configuration integrated in a single package
- With high thermal conductivity DBC as the Insulation
- Welding by vacuum welding technology, which provide high reliability

Parameter	Value	Unit
V_{RRM}	1800	V
$I_{T(AV)}(@ T_C = 85^\circ\text{C})$	320	A
$I_{TSM}(@ t_p = 10\text{ms})$	9500	A
$V_T(\text{Max})$	1.80	V

Applications

- Temperature control
- Light control system
- DC motor



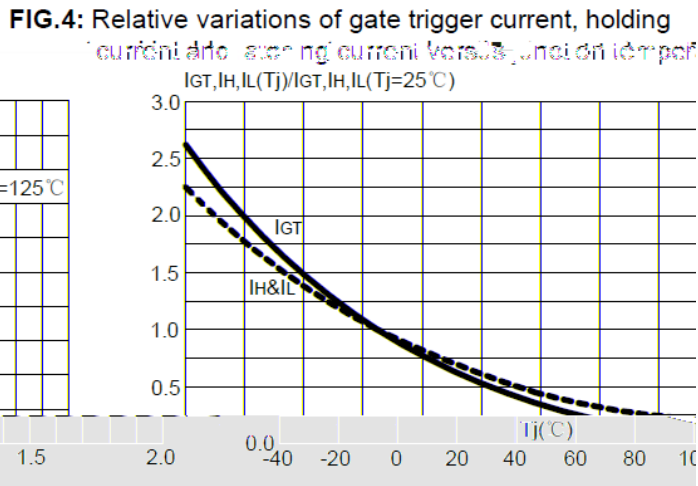
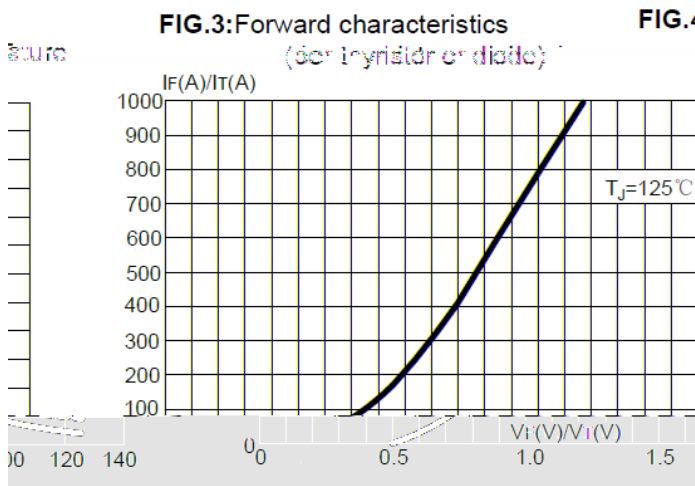
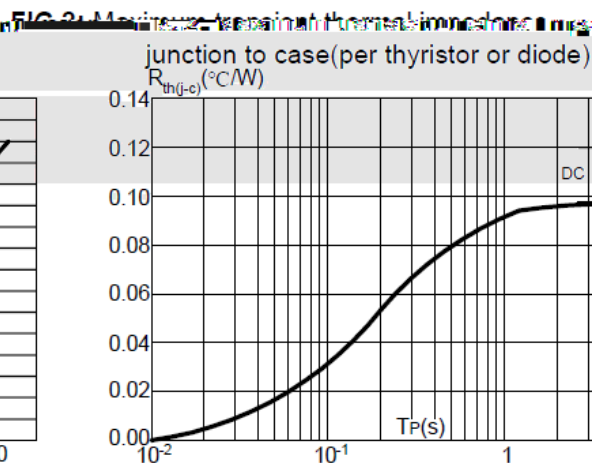
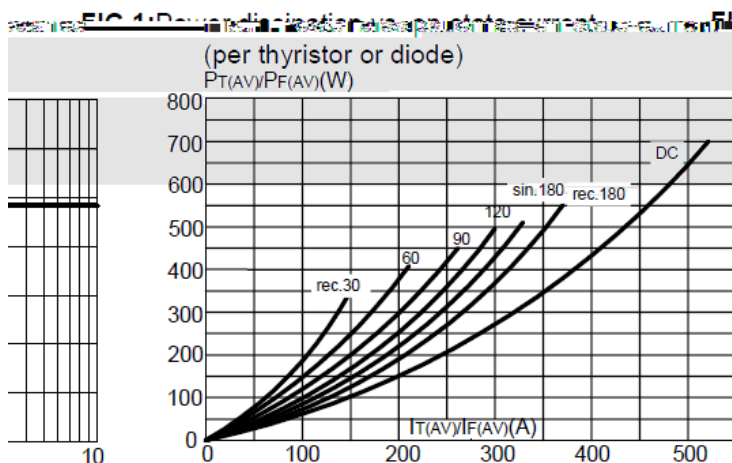
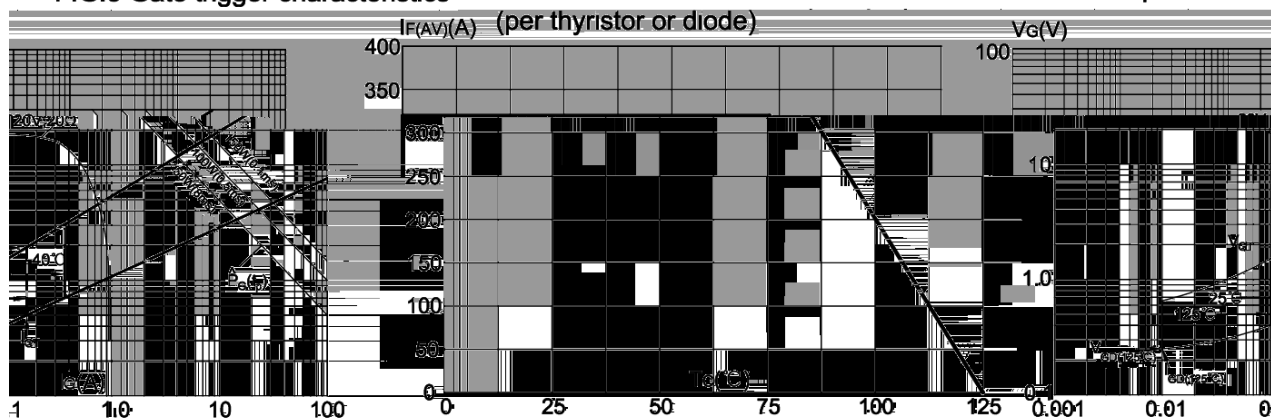
Absolute maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

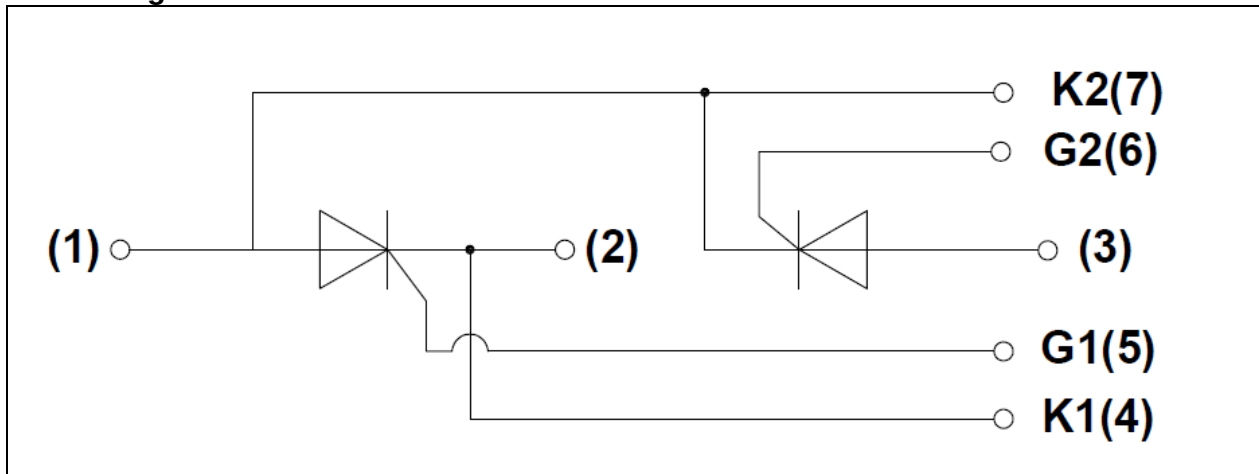
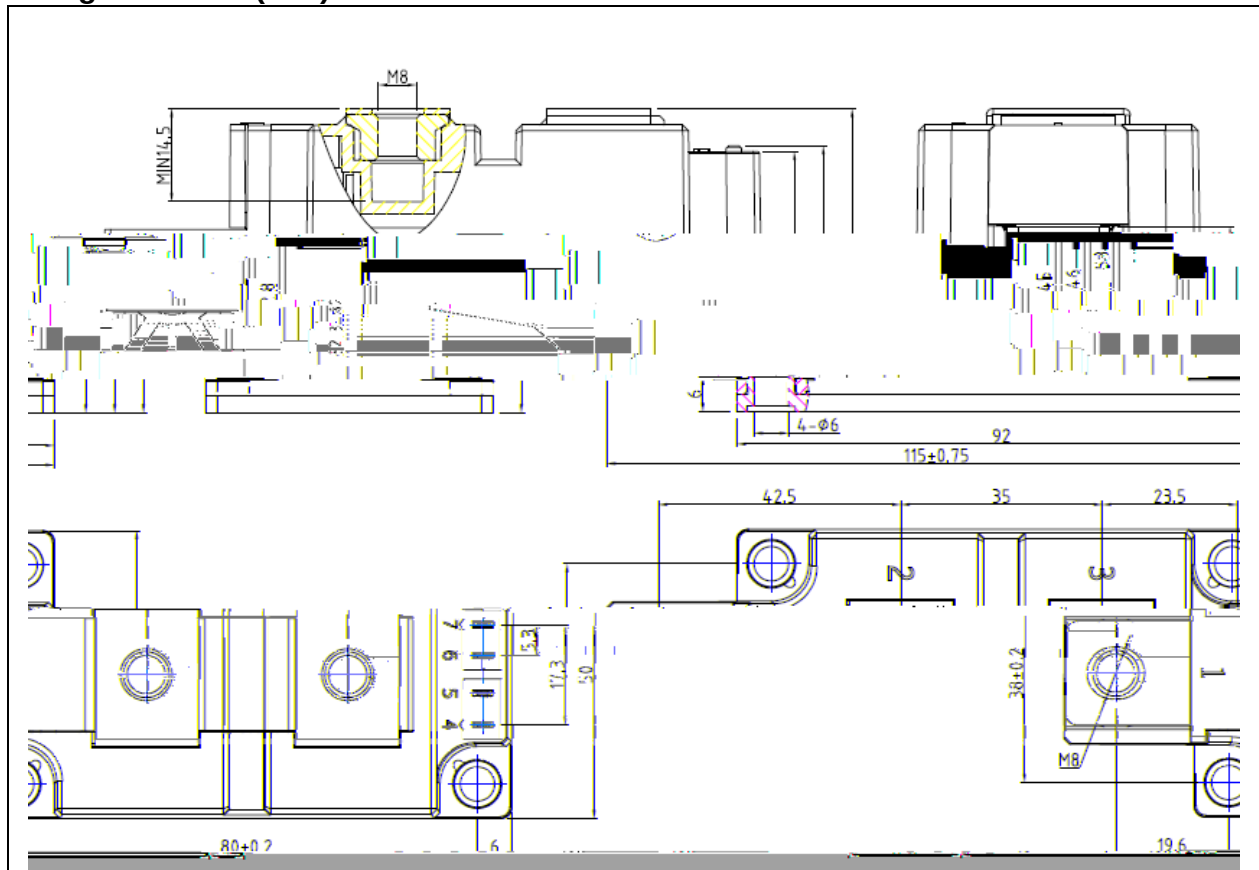
Parameter	Conditions	Symbol	Values	Unit
Repetitive peak off-state voltage	$T_{vj} = 25^\circ\text{C}$	V_{DRM}	1800	V
Repetitive peak reverse voltage	$T_{vj} = 25^\circ\text{C}$	V_{RRM}	1800	V
Non-repetitive peak off-state voltage	$T_{vj} = 25^\circ\text{C}$	V_{DSM}	1900	V
Non-repetitive peak reverse voltage	$T_{vj} = 25^\circ\text{C}$	V_{RSM}	1900	V
Average forward current	$T_C = 85^\circ\text{C}$	$I_{T(AV)}$	320	A
Forward surge current	1/2 cycle, Sine wave, 50Hz $T_{vj} = 25$	I_{TSM}	9500	A
I^2t value for fusing		I^2t	450000	A^2s
Critical rate of rise of on-state current	$I_G = 2 \times I_{GT}$	di/dt	150	A/s
RMS isolation voltage	A.C 50Hz(1s/1min)	V_{ISO}	3600/3000	V



**Ordering Information**

Device	Marking	Package	Weight	Inner Box	Per Carton
JMT320KT18T3	JMT320KT18T3	T3	355±10g/PCS	3 PCS	27 PCS

Typical Electrical & Thermal Characteristics**FIG.5 Gate trigger characteristics****FIG.6: Forward current vs. case temperature**

Circuit Diagram

Package Outlines (mm)

Package Outlines (mm)



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